

**IGBT Modules** 

#### Power Module (V series) 1200V / 400A / 1-in-1 package

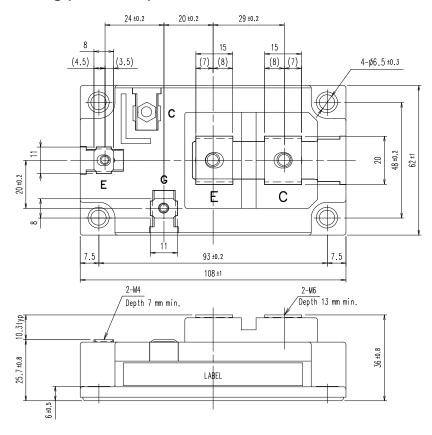
#### ■ Features

High speed switching Voltage drive Low Inductance modul structure

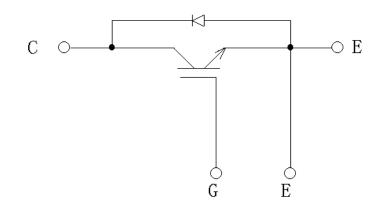
#### ■ Applications

Inverter for Motor Drives, AC and DC Servo Drives Amplifier Uninterruptible Power Supply ,Industrial machines,Such as Welding machines

#### ■ Outline drawing (Unit:mm)



#### **■** Equivalent Circuit



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#### ■ Absolute Maximum Ratings (at T<sub>C</sub>= 25°C unless otherwise specified)

	Items	Symbols	Cond	litions	Maximum Ratings	Units
Collector-Emitter voltage		V <sub>CES</sub>			1200	V
Gate-Emi	ter voltage	$V_{GES}$			±20	V
-		,	Continuous	T <sub>C</sub> =100°C	400	
		/c		T <sub>C</sub> =25°C	480	1
Collector	current	I <sub>C RM</sub>	1ms		800	Α
		-1 <sub>C</sub>			400	
			1ms		800	
Collector power dissipation		Pc	1 device		3330	W
Junction temperature		$T_{\rm j}$			175	
Operating	Operating junction temperature				450	
(under sw	(under switching conditions)				150	°C
Case temperature		T <sub>c</sub>			125	
Storage temperature		$T_{\rm stg}$			-40 ~ 125	
Isolation	between terminal and copper base(*1)	V <sub>iso</sub>	AC: 1min.		2500	VAC
voltage	between terminal and copper base( 1)	v iso	AC. IIIIII.		2500	VAC
Corour	Mounting (*2)	-			6.0	
Screw Torque	Terminals (*3)	M4			2.0	Nm
Torque		M6			5.0	

(\*1) All terminals should be connected together during the test.

(\*2) Recommendable Value: 3.0-6.0 Nm (M5,M6)
 (\*3) Recommendable Value: 1.1-2.0 Nm (M4)
 Recommendable Value: 2.5-5.0 Nm (M6)

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#### ■ Electrical characteristics (at T<sub>i</sub>= 25°C unless otherwise specified)

ltomo	Cumbala	Conditi	<b>.</b>	Ch	aracterist	ics	Linita
Items	Symbols	Conditions		min.	typ.	max.	Units
Zero gate voltage Collector current	I <sub>CES</sub>	VGE=0V,VCE=1200V		-	-	4.0	mA
Gate-Emitter leakage current	I <sub>GES</sub>	VCE=0V,VGE=±20V		-	1	400	nA
Gate-Emitter threshold voltage	$V_{GE(th)}$	VCE=20V,Ic=400	0mA	6.0	6.5	7.0	V
	1/	VOE 45V	T <sub>j</sub> =25°C	-	1.95	2.40	
	V <sub>CE(sat)</sub> (terminal)	VGE=15V Ic=400A	T <sub>j</sub> =125°C	-	2.25	-	
Collector-Emitter	(terrillial)	10-400/	T <sub>j</sub> =150°C	-	2.30	-	
saturation voltage	17	1,05 4514	T <sub>j</sub> =25°C	-	1.75	2.15	7
	V <sub>CE(sat)</sub>	VGE=15V Ic=400A	T <sub>j</sub> =125°C	-	2.05	-	1
	(chip)	IC=400A	T <sub>i</sub> =150°C	-	2.10	-	-
Internal gate resistance	$R_{g(int)}$	-	1.	-	1.9	-	Ω
Input capacitance	Cies	VCE=10V, VGE	=0V, f=1MH	-	36	-	nF
	t <sub>on</sub>			-	600	-	
Turn-on time	t <sub>r</sub>	Vcc=600V,Ic=40	-	200	-	nsec	
	$t_{r(i)}$	VGE=±15V,Rg=1.8Ω,		-	80		-
Turn-off time	t off	Tj=150°C,Ls=35	nH	-	1000	-	
Tuni-on time	$t_{f}$	-	-	140	-		
Farmed an arthur	1/	VOE 0V	$T_j=25^{\circ}C$	-	1.85	2.35	V V Ω nF
	V <sub>F</sub> (terminal)	VGE=0V IF=400A	T <sub>j</sub> =125°C	-	2.00	-	
	(terrillial)	II =400A	T <sub>j</sub> =150°C	-	1.95	-	7 ,,
Forward on voltage	.,		T <sub>j</sub> =25°C	-	1.70	2.15	_ v
	V <sub>F</sub>	VGE=0V	T <sub>i</sub> =125°C	-	1.85	-	
	(chip)	IF=400A	T <sub>i</sub> =150°C	-	1.80	-	1
Reverse recovery time	,		1 '	-	200	-	nsec

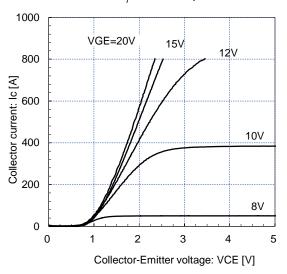
#### 5. Thermal resistance characteristics

Items	Symbols	Conditions	Ch	aracterist	ics	Units	
ILEIIIS	Syllibols	Conditions	min.	typ.	max.	Ullits	
Thermal resistance	$R_{\text{th(j-c)}}$	IGBT	-	-	0.045		
(1device)	/ th(j-c)	FWD	-	-	0.077	K/W	
Contact thermal resistance (1device) (*1)	$R_{ m th(c-f)}$	with thermal compound	-	0.0125	-	10,00	

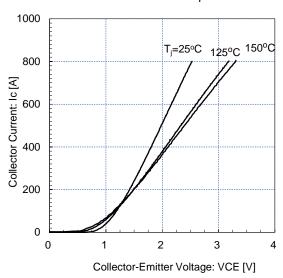
<sup>(\*1)</sup> This is the value which is defined mounting on the additional cooling fin with thermal compound.

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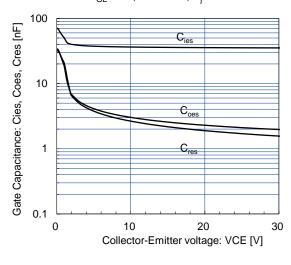
Collector current vs. Collector-Emitter voltage  $T_i = 25^{\circ}C$  / chip



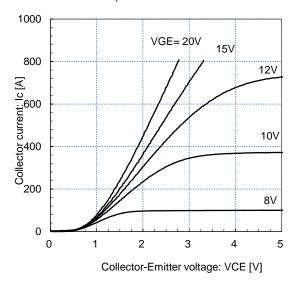
Collector current vs. Collector-Emitter voltage VGE = 15V / chip



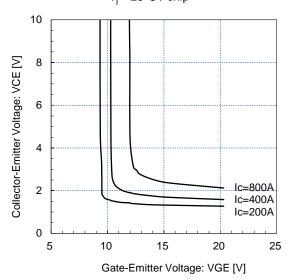
Gate Capacitance vs. Collector-Emitter Voltage  $V_{GF} = 0V$ , f = 1MHz,  $T_i = 25$ °C



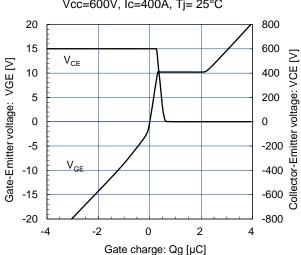
Collector current vs. Collector-Emitter voltage (typ.)  $T_i = 150^{\circ}C$  / chip



Collector-Emitter voltage vs. Gate-Emitter voltage  $T_i = 25^{\circ}C$  / chip

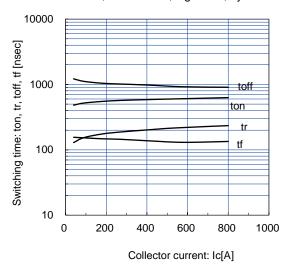


Dynamic Gate Charge (typ.) Vcc=600V, Ic=400A, Tj= 25°C

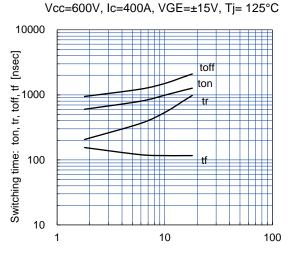


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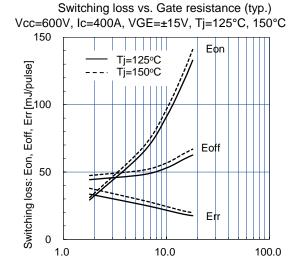
Switching time vs. Collector current (typ.) Vcc=600V, VGE=±15V, Rg=1.8Ω, Tj=125°C



Switching time vs. Gate resistance (typ.)

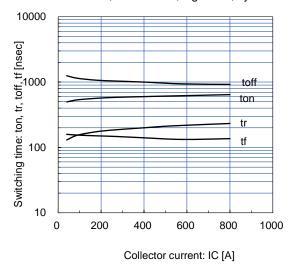


Gate resistance: Rg  $[\Omega]$ 



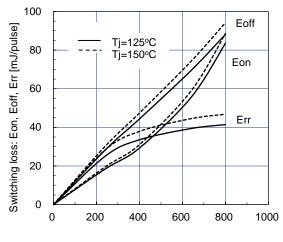
Gate resistance: Rg  $[\Omega]$ 

Switching time vs. Collector current (typ.) Vcc=600V, VGE=±15V, Rg=1.8Ω, Tj=150°C



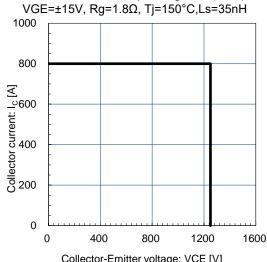
Switching loss vs. Collector current (typ.)

Vcc=600V, VGE=±15V, Rg=1.8Ω, Tj=125°C, 150°C



Collector current: Ic [A]

Reverse bias safe operating area (max.)



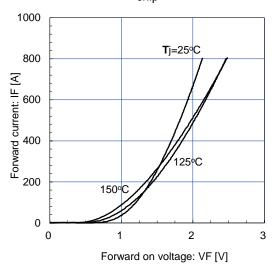
Collector-Emitter voltage: VCE [V] (Main terminals)

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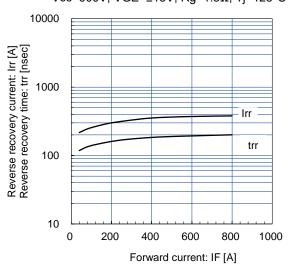


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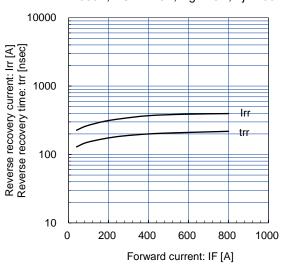
Forward current vs. Forward vltage (typ.)



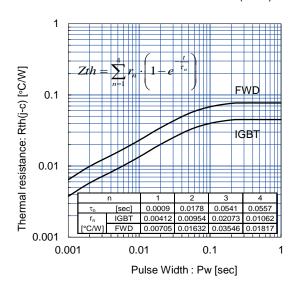
Reverse recovery characteristics (typ.) Vcc=600V, VGE=±15V, Rg=1.8Ω, Tj=125°C



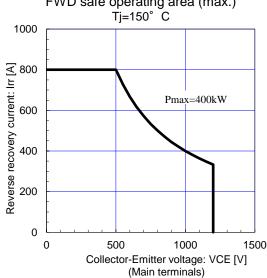
Reverse Recovery Characteristics (typ.) Vcc=600V, VGE=±15V, Rg=1.8Ω, Tj= 150°C



Transient Thermal Resistance (max.)



FWD safe operating area (max.)



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